

FCA65S20D1QA

eSiC Automotive Silicon Carbide Schottky Diode

650V, 20A



Description

The 650V eSiC is an advanced Faster Semiconductor's silicon carbide diode family. This technology combines the benefits of excellent low capacitive charge and robustness. Consequently, the eSiC family is suitable for application requiring high power efficiency.

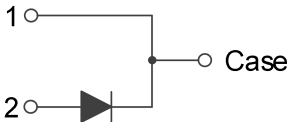
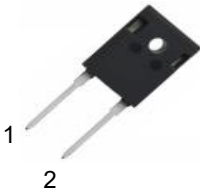
Applications

- OBC (On Board Charger)
- DC/DC Converter for EV/HEV
- Wireless Charger

Features

V_{RRM}	I_F	$T_{J,max}$	Q_C
650 V	20 A	175 °C	62 nC

- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- AEC Q101 Qualified
- Pb-Free, Halogen Free and RoHS compliant



Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
I_F	Forward Current	$T_C=128^{\circ}C$	20	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C=25^{\circ}C, t_p=10\text{ ms}$	95	A
		$T_C=150^{\circ}C, t_p=10\text{ ms}$	80.8	A
$I_{F,Max}$	Non-Repetitive Peak Forward Current	$T_C=25^{\circ}C, t_p=10\text{ us}$	880	A
		$T_C=150^{\circ}C, t_p=10\text{ us}$	748	A
$I^2dt\text{ value}$	$\int i^2t$	$T_C=25^{\circ}C, t_p=10\text{ ms}$	45.1	A ² S
		$T_C=150^{\circ}C, t_p=10\text{ ms}$	32.6	A ² S
P_{tot}	Power Dissipation	$T_C=25^{\circ}C$	121	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.24	°C/W

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
FCA65S20D1QA	FCA65S20D1QA	TO-247-2L	Tube	30 units

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F =20 A, T _C =25°C		1.40	1.7	V
		I _F =20 A, T _C =175°C		1.55	-	
I _R	Reverse Current	V _R =650 V, T _C =25°C		-	100	μA
		V _R =650 V, T _C =175°C		-	300	
Q _C	Total Capacitive Charge	V _R =400 V, T _C =25°C		62		nC
C	Total Capacitance	V _R =1 V, f=100 kHz		1010		pF
		V _R =400 V, f=100 kHz		99		
E _C	Capacitance Stored Energy	V _R =400 V, T _C =25°C		9.2		μJ

Typical Performance Characteristics

Figure 1. Power Derating

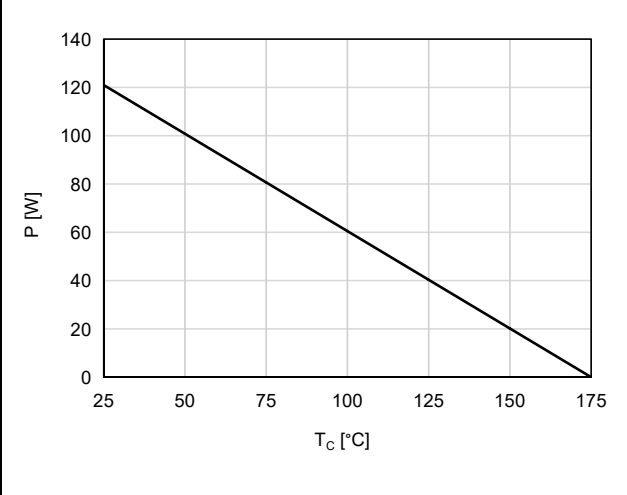


Figure 2. Current Derating

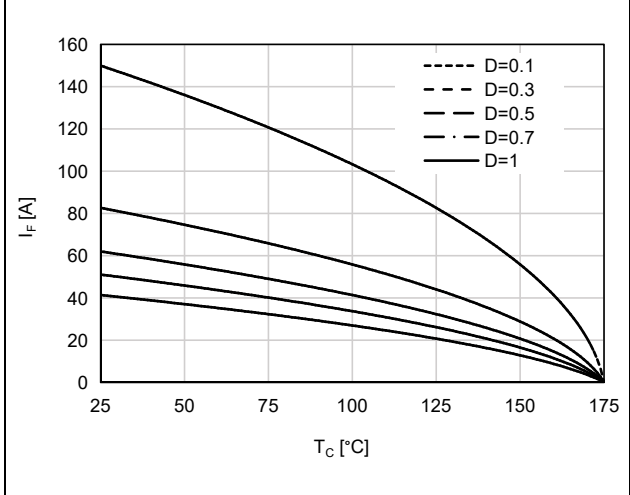


Figure 3. Forward Characteristics

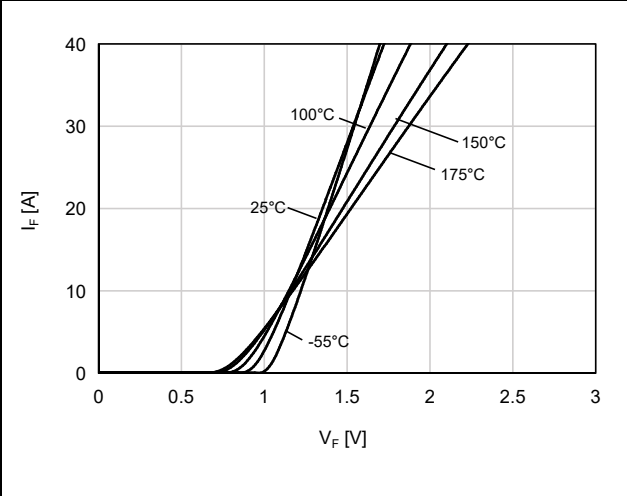


Figure 4. Reverse Characteristics

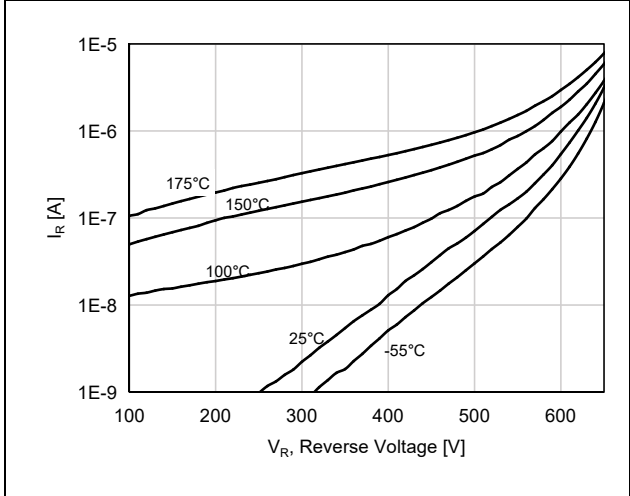


Figure 5. Capacitive Charge Characteristic

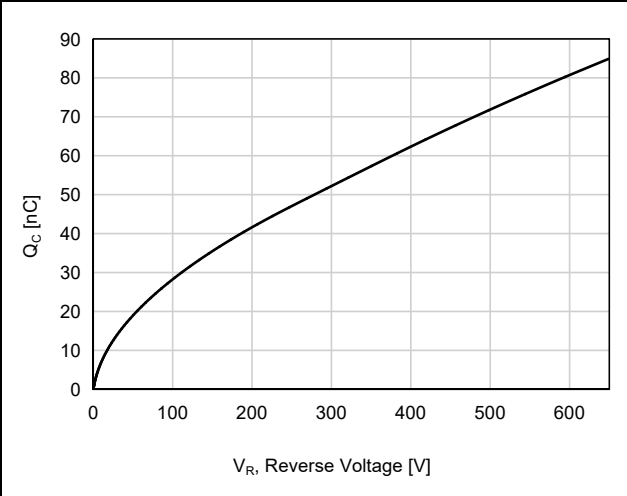
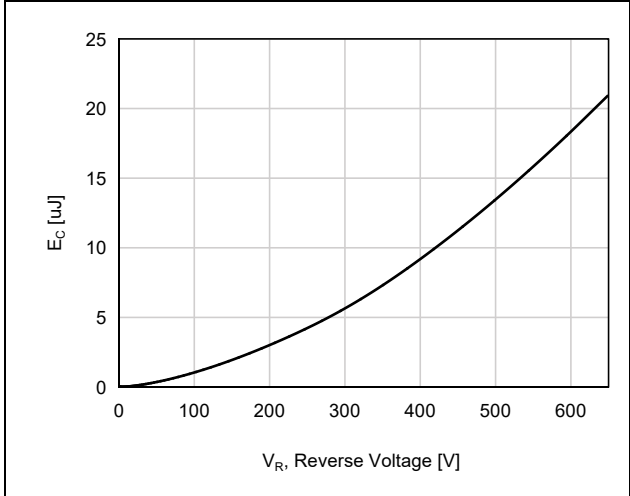


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics

Figure 7. Capacitance Characteristic

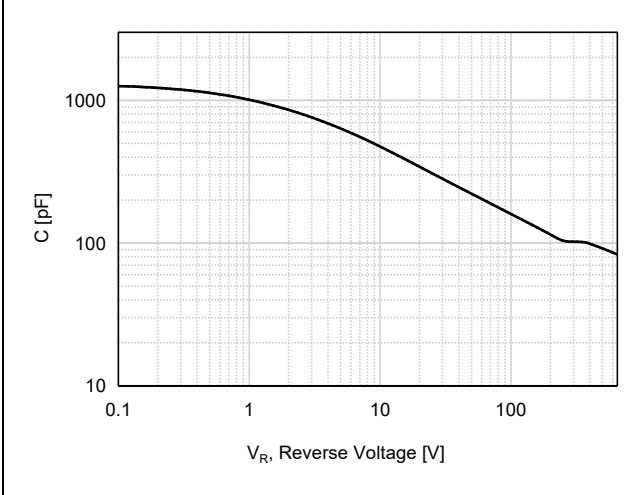
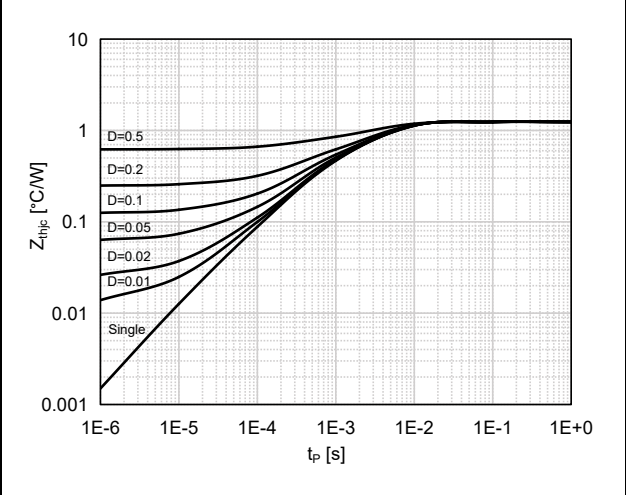
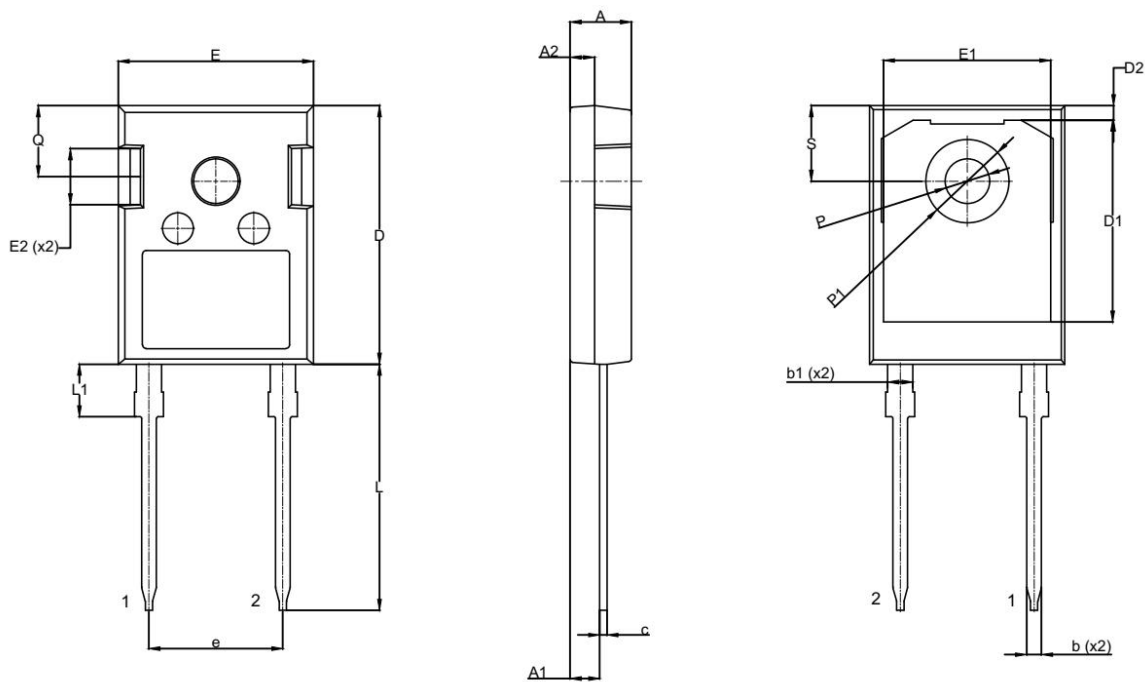


Figure 8. Transient Thermal Response Curve



Package Outlines

TO-247-2L



SYMBOL	Common		
	DIMENSIONS MILLIMETER		
	MIN.	NOM.	MAX.
A	4.80	5.00	5.20
A1	2.29	2.42	2.54
A2	1.90	2.00	2.10
b	1.10	1.20	1.30
b1	1.91	2.06	2.20
c	0.50	0.60	0.70
D	20.80	21.07	21.34
D1	16.26	16.46	16.66
D2	0.97	1.17	1.37
E	15.75	15.94	16.13
E1	13.46	13.66	13.86
E2	4.32	4.58	4.83
e	10.92 BSC.		
L	19.85	20.05	20.25
L1	4.05	4.27	4.48
P	3.56	3.61	3.66
P1	6.75	6.80	6.85
Q	5.38	5.79	6.20
S	6.15 BSC.		